

In accordance with 37 CFR § 1.97, this Supplemental Information Disclosure Statement is not to be construed as a representation that a search has been made or that no other possibly material information as defined under 37 CFR § 1.56(a) exists.

The patents and/or publications submitted herewith are set forth on the attached Form PTO-1449.

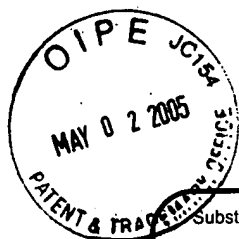
Applicants certify that all references submitted with this disclosure were first cited in a communication from a foreign patent office dated February 14, 2005, which communication is enclosed, not more than three months prior to the filing of this Supplemental Information Disclosure Statement.

If the sum of \$180.00 is due under 37 CFR § 1.17(p) pursuant to § 1.97, the Commissioner is hereby authorized to charge this fee, and any other fee necessary to make this submission timely, to the Deposit Account No. 20-0782/AMAT/8764P1/KMT.

Respectfully submitted,



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Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

Sheet 2 of 2

Complete if Known

Application Number	10/758,758
Filing Date	January 15, 2004
First Named Inventor	Luc Van Autryve
Art Unit	2812
Examiner Name	Unassigned
Attorney Docket Number	AMAT/8764P1/FEP/OXD/JW

NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
	C1	Article by Valentini et al., "Effect fo thermal annealing on the electronic properties of nitrogen doped amorphous carbon/p-type crystalline silicon heterojunction diodes", American Vacuum Society, 2003, pgs. 582-588.	
	C2	Article by Barradas et al., "Growth and characterization of amorphous carbon films doped with nitrogen", Nuclear Instruments and Methods in Physics Research B, 161-163 (2000) pgs 969-974.	
	C3	Article by Kuo et al., "Field emission studies of low-temperature thermal annealing of nitrogen-doped hydrogenated amorphous carbon (a-C:H:N) films", Diamond and Related Materials 10 (2001) pgs 889-894.	
	C4	Article by Zhang et al., "Raman analysis of laser annealed nitrogen doped amorphous carbon film", Solid State Communications 123 (2002) pgs 97-100.	
	C5	PCT International Search Report from International Application No. PCT/US 2004/032151, dated February 14, 2005	

Examiner
SignatureDate
Considered

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Applicant's unique citation designation number (optional). ² Applicant is to place a check mark here if English language Translation is attached.

This collection of information is required by 37 CFR 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 120 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

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